

What is claimed is:

1. A plating method, comprising:

filling a plating liquid containing metal ions and an additive
5 into a plating space formed between a substrate and an anode disposed
closely to the substrate so as to face the substrate; and
changing the concentration of the additive in the plating
liquid filled into said plating space during a plating process.

10 2. The plating method according to claim 1, wherein the
concentration of the additive in the plating liquid is adjusted
by intermittently supplying the plating liquid into said plating
space.

15 3. The plating method according to claim 1, wherein the
concentration of the additive in the plating liquid is adjusted
by supplementary addition of the additive to said plating space.

20 4. The plating method according to claim 1, wherein the
concentration of the additive in the plating liquid is adjusted
by removal of the additive in the plating liquid.

25 5. The plating method according to claim 1, wherein the
additive is a brightener, and the concentration of the brightener
at the middle and later stages of the plating process is lower than
that at the initial stage of the plating process.

6. The plating method according to claim 1, wherein the

additive is a leveler, and the concentration of the leveler at the middle and later stages of the plating process is higher than that at the initial stage of the plating process.

5 7. A plating apparatus, comprising:

 a substrate holder for holding a substrate so that a current can flow from a cathode to the substrate;

 an anode opposed to the substrate held by said substrate holder; and

10 a plating liquid introducing device for introducing a plating liquid into a plating space formed between the substrate and said anode in a batch process or an intermittent process.

15 8. The plating apparatus according to claim 7, wherein a plating liquid impregnation material is provided in said plating space.

20 9. The plating apparatus according to claim 7, further comprising a liquid introducing device for introducing into said plating space a liquid having a different additive concentration from the additive concentration of the plating liquid.

25 10. The plating apparatus according to claim 9, wherein a plating liquid impregnation material is provided in said plating space.

 11. The plating apparatus according to claim 7, further comprising a temperature adjusting device for adjusting the

temperature of the plating liquid in said plating space.

12. A plating apparatus, comprising:

5 a substrate holder for holding a substrate so that a current
can flow from a cathode to the substrate;

an anode opposed to the substrate held by said substrate
holder; and

10 a moving device for moving a portion of the substrate facing
said anode in such a state that an inner central portion of the
surface of the substrate faces said anode for a longer time than
an outer peripheral portion of the surface of the substrate faces
said anode.

13. The plating apparatus according to claim 12, wherein said
15 moving device comprises a substrate-rotating device for rotating
the substrate.

14. The plating apparatus according to claim 12, wherein said
20 moving device comprises an anode-rotating device for rotating said
anode.

15. The plating apparatus according to claim 12, wherein said
moving device comprises an anode-translating device for
translating said anode.

16. A plating apparatus, comprising:

a substrate holder for holding a substrate so that a current
can flow from a cathode to the substrate; and

an anode opposed to the substrate held by said substrate holder,

wherein the distance between said anode and an inner central portion of the substrate is smaller than the distance between said
5 anode and an outer peripheral portion of the substrate.

17. A plating apparatus, comprising:

a substrate holder for holding a substrate so that a current can flow from a cathode to the substrate;

10 an anode opposed to the substrate held by said substrate holder; and

a distance changing device for changing the distance between the substrate and said anode after initiation of plating.

15 18. A plating method, comprising:

disposing a substrate and an anode in such a state that the substrate faces said anode;

flowing a current between the substrate and said anode while supplying a plating liquid therebetween; and

20 moving a portion of the substrate facing said anode in such a state that an inner central portion of the surface of the substrate faces said anode for a longer time than an outer peripheral portion of the surface of the substrate faces said anode.

25 19. The plating method according to claim 18, wherein the portion of the substrate facing said anode is moved by rotation of the substrate.

20. The plating method according to claim 18, wherein the portion of the substrate facing said anode is moved by rotation of said anode.

5 21. The plating method according to claim 18, wherein the portion of the substrate facing said anode is moved by translation of said anode.

10 22. A plating method, comprising:
 disposing a substrate and an anode so that the substrate faces
 said substrate; and
 flowing a current between the substrate and said anode while
 supplying a plating liquid therebetween,
 wherein the distance between said anode and an inner central
15 portion of the substrate is smaller than the distance between said
 anode and an outer peripheral portion of the substrate.

 23. A plating method, comprising:
 disposing a substrate and an anode so that the substrate faces
20 said anode;
 flowing a current between the substrate and said anode while
 supplying a plating liquid therebetween; and
 changing the distance between the substrate and said anode
 after initiation of plating.

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